

L Number	Hits	Search Text	DB	Time stamp
1	440	deposit\$3 near3 nitride with gate adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/17 21:15
2	155	(deposit\$3 near3 nitride with gate adj oxide) and @ad<19931130	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/17 21:16
3	231	(deposit\$3 near3 nitride with gate adj oxide) same (polysilicon polycrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/17 21:16
4	58	((deposit\$3 near3 nitride with gate adj oxide) same (polysilicon polycrystalline)) and @ad<19931130	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/17 21:16